IN74HC4051A

Analog Multiplexer Demultiplexer High-Performance Silicon-Gate CMOS

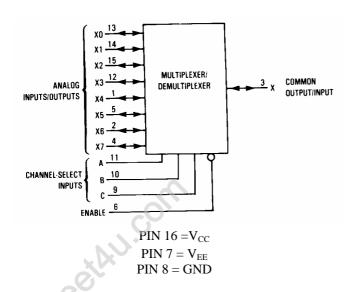
The IN74HC4051A utilize silicon-gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. These analog multiplexers/demultiplexers control analog voltages that may vary across the complete power supply range (from $V_{\rm CC}$ to $V_{\rm FF}$).

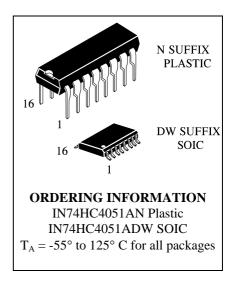
The Channel-Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input.When the Enable pin is high, all analog switches are turned off.

The Channel-Select and Enable inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range (V_{CC}-V_{EE})=2.0 to 12.0 V
- Digital (Control) Power Supply Range (V_{CC}-GND)=2.0 to 6.0 V
- Low Noise

LOGIC DIAGRAM Single-Pole, 8-Position Plus Common Off





PIN ASSIGNMENT

X4 [1 •	16 V _{CC}
X6 🛚	2	15 X2
ΧГ	3	14 X1
X7 [4	13 X0
X5 [5	12 X3
ENABLE [6	11 🛭 A
${ m v_{EE}}$ [7	10 B
V _{EE} L GND [8	9 🛘 C

FUNCTION TABLE

Co	ON			
Enable		Select		Channels
	C	В	A	
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	X3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
Н	X	X	X	None

X = don't care



MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	Positive DC Supply Voltage (Referenced to GND) (Referenced to V_{EE})	-0.5 to +7.0 -0.5 to +14.0	V
V_{EE}	Negative DC Supply Voltage (Referenced to GND)	-7.0 to +0.5	V
V _{IS}	Analog Input Voltage	V_{EE} - 0.5 to V_{CC} +0.5	V
V_{IN}	Digital Input Voltage (Referenced to GND)	-1.5 to V _{CC} +1.5	V
I	DC Input Current Into or Out of Any Pin	±25	mA
P_{D}	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
Tstg	Storage Temperature	-65 to +150	°C
T_{L}	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	Positive Supply Voltage (Referenced to GND) (Referenced to V_{EE})	2.0 2.0	6.0 12.0	V
V_{EE}	Negative DC Supply Voltage (Referenced to GND)	- 6.0	GND	V
$V_{\rm IS}$	Analog Input Voltage	V_{EE}	V_{CC}	V
$V_{\rm IN}$	Digital Input Voltage (Referenced to GND)	GND	V_{CC}	V
${ m V_{IO}}^*$	Static or Dynamic Voltage Across Switch	-	1.2	V
T_A	Operating Temperature, All Package Types	-55	+125	°C
$t_{\rm r},t_{\rm f}$	Input Rise and Fall Time (Channel Select V_{CC} = 2.0 V or Enable Inputs) V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0	1000 500 400	ns

^{*} For voltage drops across the switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i. e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range indicated in the Recommended Operating Conditions..

Unused digital input pins must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused Analog I/O pins may be left open or terminated.



⁺Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

$\textbf{DC ELECTRICAL CHARACTERISTICS} \ \ \text{Digital Section (Voltages Referenced to GND)} \ \ V_{EE} = GND,$

Except Where Noted

			V_{CC}	Guara	anteed Li	imit	
Symbol	Parameter	Test Conditions	V	25 °C to -55°C	≤85 °C	≤125 °C	Unit
V _{IH}	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R _{ON} = Per Spec	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{IL}	Maximum Low -Level Input Voltage, Channel-Select or Enable Inputs	R _{ON} = Per Spec	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
$I_{\rm IN}$	Maximum Input Leakage Current, Channel-Select or Enable Inputs	$V_{IN}=V_{CC}$ or GND, $V_{EE}=-6.0$ V	6.0	±0.1	±1.0	±1.0	μА
I_{CC}	Maximum Quiescent Supply Current (per Package)	$\begin{aligned} & \text{Channel Select} = V_{CC} \text{ or GND} \\ & \text{Enable} = V_{CC} \text{ or GND} \\ & V_{IS} = V_{CC} \text{ or GND} \\ & V_{IO} = 0 \text{ V} \qquad V_{EE} = \text{GND} \end{aligned}$	6.0	2	20	40	μΑ
		$V_{EE} = -6.0$	6.0	8	80	160	

DC ELECTRICAL CHARACTERISTICS Analog Section

			V_{CC}	V_{EE}	Guarar	iteed L	imit	
Symbol	Parameter	Test Conditions	V	V	25 °C to -55°C	≤85 °C	≤125 °C	Unit
R _{ON}	Maximum "ON" Resistance	$\begin{aligned} &V_{IN} {=} V_{IL} \text{ or } V_{IH} \\ &V_{IS} {=} V_{CC} \text{ or } V_{EE} \\ &I_S {\leq} 2.0 \text{ mA(Figure 1)} \end{aligned}$	4.5 4.5 6.0	0.0 -4.5 -6.0	190 120 100	240 150 125	280 170 140	Ω
		$V_{IN}=V_{IL} \text{ or } V_{IH}$ $V_{IS}=V_{CC} \text{ or } V_{EE}$ (Endpoints) $I_{S} \leq 2.0 \text{ mA(Figure 1)}$	4.5 4.5 6.0	0.0 -4.5 -6.0	150 100 80	190 125 100	230 140 115	
$\Delta R_{ m ON}$	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{aligned} &V_{IN} {=} V_{IL} \text{ or } V_{IH} \\ &V_{IS} {=} \ 1/2 \ (V_{CC^-} \ V_{EE}) \\ &I_S {\leq} \ 2.0 \ mA \end{aligned}$	4.5 4.5 6.0	0.0 -4.5 -6.0	30 12 10	35 15 12	40 18 14	Ω
I_{OFF}	Maximum Off- Channel Leakage Current, Any One Channel	$V_{IN}=V_{IL}$ or V_{IH} $V_{IO}=V_{CC}-V_{EE}$ Switch Off (Figure 2)	6.0	-6.0	0.1	0.5	1.0	μΑ
	Maximum Off- Channel Leakage Current, Common Channel	$V_{IN}=V_{IL}$ or V_{IH} $V_{IO}=V_{CC}-V_{EE}$ Switch Off (Figure 3)	6.0	-6.0	0.2	2.0	4.0	
I _{ON}	Maximum On- Channel Leakage Current, Channel to Channel	$V_{IN}=V_{IL}$ or V_{IH} Switch to Switch = V_{CC} - V_{EE} (Figure 4)	6.0	-6.0	0.2	2.0	4.0	μА

$\textbf{AC ELECTRICAL CHARACTERISTICS} \text{ (C}_L = 50 \text{pF,Input } t_r = t_f = 6.0 \text{ ns)}$

				Gua	aranteed L	imit	
Symbol	Parameter	Parameter		25 °C to -55°C	≤85°C	≤125°C	Unit
t _{PLH} , t _{PHL}		Maximum Propagation Delay, Channel-Select to Analog Output (Figures 8 and 9)			465 93 79	550 110 94	ns
t_{PLH}, t_{PHL}	Maximum Propagation Delay Analog Output (Figures 10 and		2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
t_{PLZ}, t_{PHZ}	Maximum Propagation Delay , Enable to Analog Output (Figures 12 and 13)			290 58 49	364 73 62	430 86 73	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay , Enable to Analog Output (Figures 12 and 13)			345 69 59	435 87 74	515 103 87	ns
C _{IN}	Maximum Input Capacitance, Channel-Select or Enable Inputs		-	10	10	10	pF
C _{I/O}	Maximum Capacitance Analog I/O	All Switches Off	-	35	35	35	pF
	Common O/I		-	130	130	130	
	Feedthrough		-	1.0	1.0	1.0	

	Power Dissipation Capacitance (Per Package) (Figure 14)	Typical @25°C,V _{CC} =5.0 V, V _{EE} =0 V	
C_{PD}	Used to determine the no-load dynamic power consumption: $P_D \!\!=\!\! C_{PD} V_{CC}^{2} f \!\!+\!\! I_{CC} V_{CC}$	45	pF

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0.0 V)

			V_{CC}	V_{EE}	Limit*	
Symbol	Parameter	Test Conditions	V	V	25 °C	Unit
BW	Maximum On- Channel Bandwidth or Minimum Frequency Response (Figure 5)	f_{in} =1 MHz Sine Wave Adjust f_{in} Voltage to Obtain 0 dBm at V_{OS} Increase f_{in} Frequence Until dB Meter Reads -3 dB R_L =50 Ω , C_L =10 pF	2.25 4.50 6.00	-2.25 -4.50 -6.00	80 80 80	MHz
-	Off-Channel Feedthrough Isolation (Figure 6)	f_{in} = Sine Wave Adjust f_{in} Voltage to Obtain 0 dBm at V_{IS} f_{in} = 10 kHz, R_L =600 Ω , C_L =50 pF	2.25 4.50 6.00	-2.25 -4.50 -6.00	-50 -50 -50	dB
		$f_{in} = 1.0 \text{ MHz}, R_L = 50 \Omega, C_L = 10 \text{ pF}$	2.25 4.50 6.00	-2.25 -4.50 -6.00	-40 -40 -40	
-	Feedthrough Noise, Channel Select Input to	$V_{IN} \le 1$ Mhz Square Wave $(t_r = t_f = 6 \text{ ns})$ Adjust R_L at Setup so that $I_S = 0$ A Enable = GND				mV_{PP}
	Common O/I (Figure 7)	$R_L = 600 \Omega, C_L = 50 pF$	2.25 4.50 6.00	-2.25 -4.50 -6.00	25 105 135	
		$R_L = 10 \Omega$, $C_L = 10 pF$	2.25 4.50 6.00	-2.25 -4.50 -6.00	35 145 190	
THD	Total Harmonic Distortion (Figure 15)	$f_{in} = 1 \text{ kHz}, R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF}$ $THD = THD_{Measured} - THD_{Source}$ $V_{IS} = 4.0 \text{ V}_{PP} \text{ sine wave}$ $V_{IS} = 8.0 \text{ V}_{PP} \text{ sine wave}$ $V_{IS} = 11.0 \text{ V}_{PP} \text{ sine wave}$	2.25 4.50 6.00	-2.25 -4.50 -6.00	0.10 0.08 0.05	%

^{*} Limits not tested. Determined by design and verified by qualification.

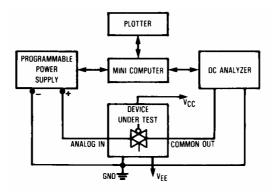


Figure 1. On Resistance Test Set-Up

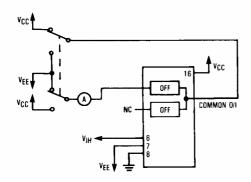


Figure 2. Maximum Off Channel Leakage Current, Any One Channel, Test Set-U_P

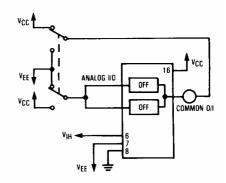


Figure 3. Maximum Off Channel Leakage Current, Common Channel, Test Set- \mathbf{U}_{P}

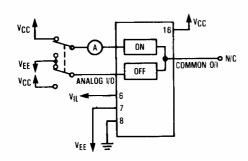
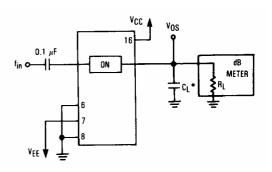
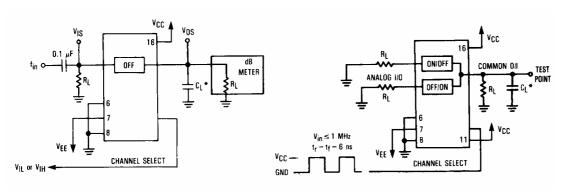


Figure 4. Maximum On Channel Leakage Current, Channel to Channel, Test Set- U_P



* Includes all probe and jig capacitance.

Figure 5. Maximum On Channel Bandwidth, $Test\ Set\mbox{-}U_P$

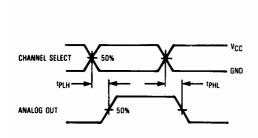


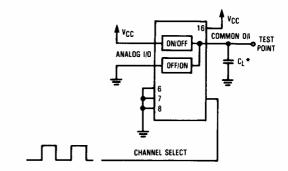
^{*} Includes all probe and jig capacitance.

Figure 6. Off Channel Feedthrough Isolation, $\label{eq:Test Set-UP} \textbf{Test Set-UP}$

* Includes all probe and jig capacitance.

Figure 7.Feedthrough Noise, Channel Select to Common Out, Test Set- U_P

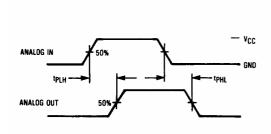


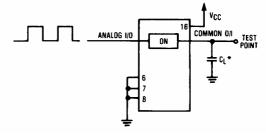


* Includes all probe and jig capacitance.

Figure 8. Switching Weveforms

Figure 9. Test Set- U_P , Channel Select to Analog Out

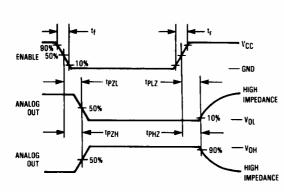




* Includes all probe and jig capacitance.

Figure 10. Switching Weveforms

Figure 11. Test Set-U_P, Analog In to Analog Out



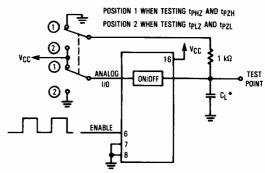
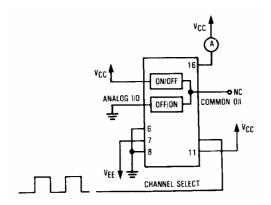
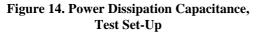
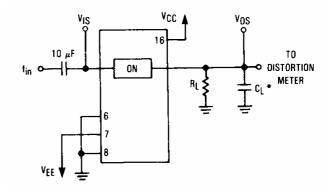


Figure 12. Switching Weveforms

Figure 13. Test Set-U_P, Enable to Analog Out



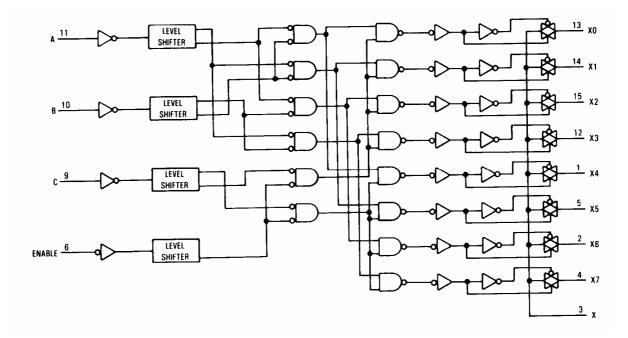




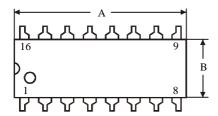
* Includes all probe and jig capacitance

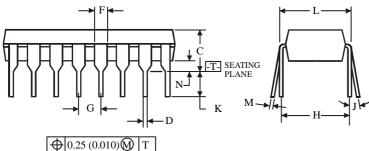
Figure 15. Total Harmonic Distortion, Test Set-U_P

EXPANDED LOGIC DIAGRAM



N SUFFIX PLASTIC DIP (MS - 001BB)





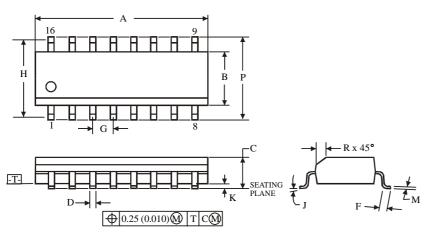
NOTES:

Dimensions "A", "B" do not include mold flash or protrusions.
 Maximum mold flash or protrusions 0.25 mm (0.010) per side.



	1				
	Dimens	ion, mm			
Symbol	MIN MAX				
A	18.67 19.69				
В	6.1 7.11				
C		5.33			
D	0.36	0.56			
F	1.14	1.78			
G	2.	54			
Н	7.	62			
J	0°	10°			
K	2.92	3.81			
L	7.62 8.26				
M	0.2 0.36				
N	0.38				

D SUFFIX SOIC (MS - 012AC)



NOTES:

- 1. Dimensions A and B do not include mold flash or protrusion.
- 2. Maximum mold flash or protrusion 0.15 mm (0.006) per side for A; for B 0.25 mm (0.010) per side.



	Dimension, mm			
Symbol	MIN	MAX		
A	9.8	10		
В	3.8 4			
C	1.35 1.75			
D	0.33 0.51			
F	0.4 1.27			
G	1.	27		
Н	5.	72		
J	0°	8°		
K	0.1	0.25		
M	0.19 0.25			
P	5.8 6.2			
R	0.25	0.5		

